



MTM761230LBF
 Silicon P-channel MOSFET

For Switching

■ Features

- Low drain-source On-state Resistance : $R_{DS(on)}$ typ. = 36 m Ω (VGS = -4 V)
- Low drive voltage : 2.5 V drive
- Halogen-free / RoHS compliant
 (EU RoHS / UL-94 V-0 / MSL : Level 1 compliant)

■ Marking Symbol : 9C

■ Packaging

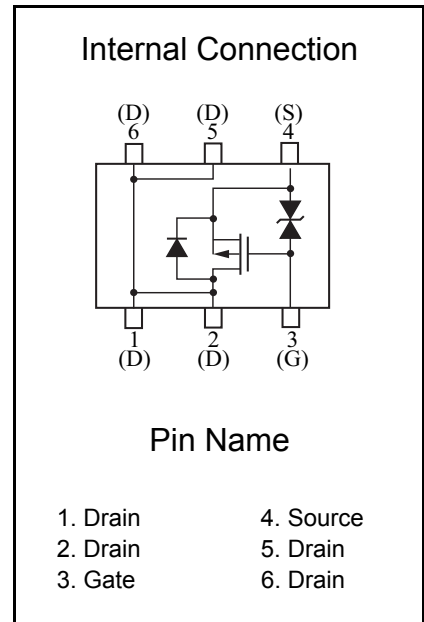
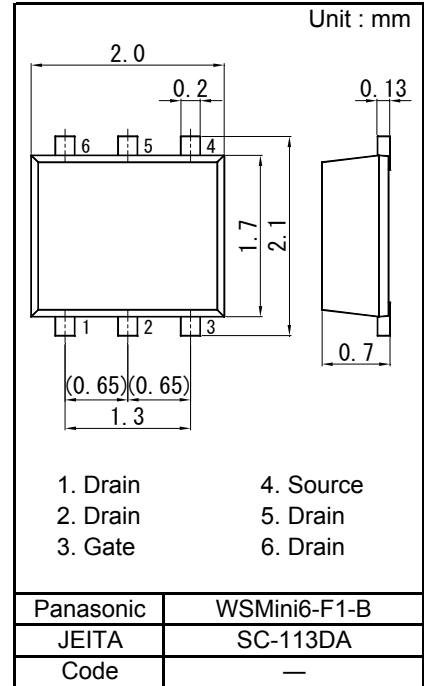
Embossed type (Thermo-compression sealing) : 3 000 pcs / reel (standard)

■ Absolute Maximum Ratings Ta = 25 °C

Parameter	Symbol	Rating	Unit
Drain to Source Voltage	VDS	-20	V
Gate to Source Voltage	VGS	±10	V
Drain Current	ID	-3	A
Drain Current (Pulsed) *1	IDp	-16	A
Total Power Dissipation *2	PD	700	mW
Channel Temperature	Tch	150	°C
Operating Ambient Temperature	Topr	-40 to +85	°C
Storage Temperature Range	Tstg	-55 to +150	°C

Note) *1 Pulse width \leq 10 μ s, Duty cycle \leq 1 %

*2 Measuring on ceramic board at 40 mm \times 38 mm \times 0.1 mm
 Absolute maximum rating PD Non-heat sink shall be made 150 mW.



■ Electrical Characteristics Ta = 25 °C ± 3 °C

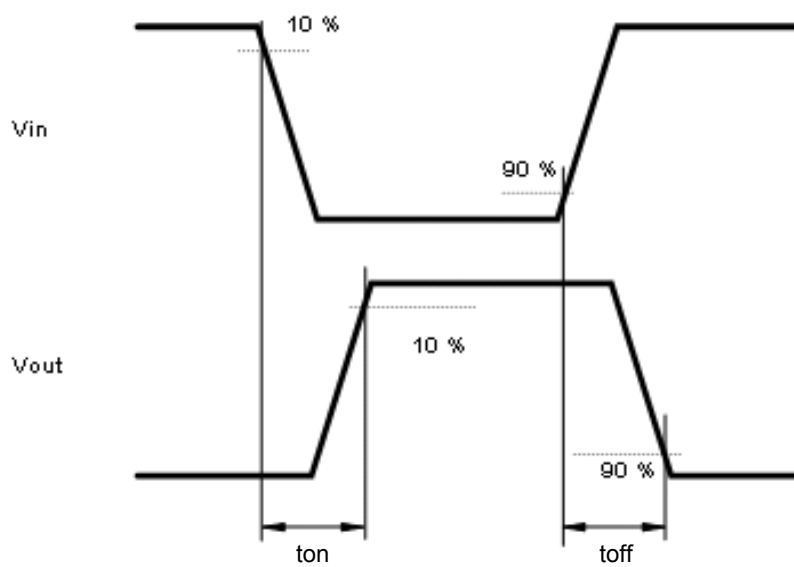
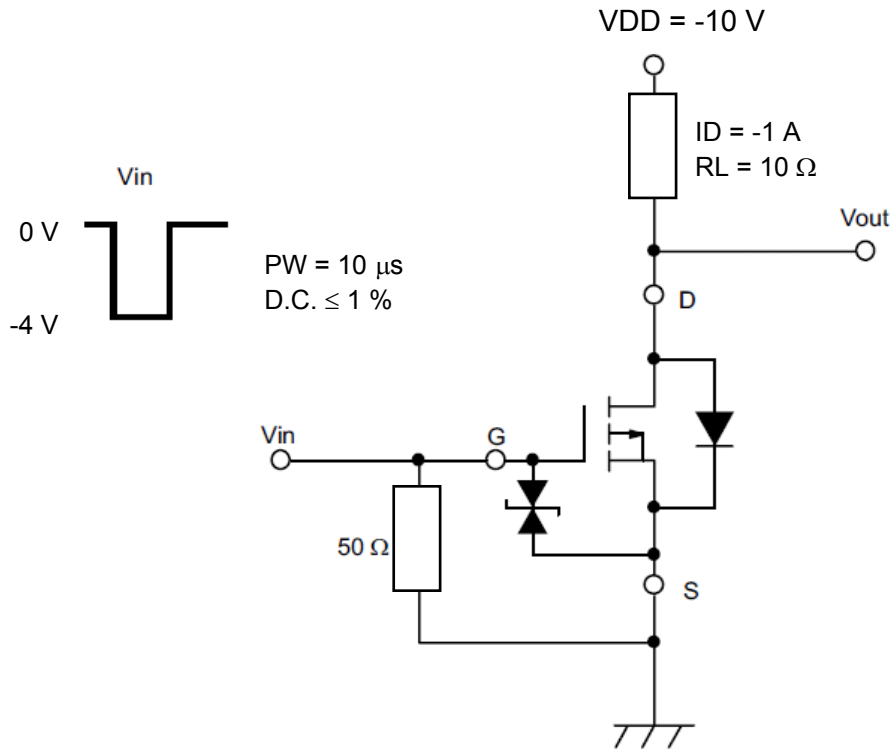
Parameter	Symbol	Conditions	Min	Typ	Max	Unit
Drain-source Breakdown Voltage	VDSS	ID = -1 mA, VGS = 0 V	-20			V
Zero Gate Voltage Drain Current	IDSS	VDS = -20 V, VGS = 0 V			-1	μA
Gate-source Leakage Current	IGSS	VGS = ±8 V, VDS = 0 V			±10	μA
Gate-source Threshold Voltage	Vth	ID = -1 mA, VDS = -10 V	-0.4	-0.85	-1.3	V
Drain-source On-state Resistance *1	RDS(on)1	ID = -1 A, VGS = -4 V		36	55	mΩ
	RDS(on)2	ID = -0.5 A, VGS = -2.5 V		42	70	
Forward transfer admittance *1	Yfs	ID = -1 A, VDS = -10 V, f = 1 kHz	3.5			S
Input Capacitance	Ciss	VDS = -10 V, VGS = 0 V f = 1 MHz		1 000		pF
Output Capacitance	Coss			100		
Reverse Transfer Capacitance	Crss			100		
Turn-on Delay Time *2	ton	VDD = -10 V, VGS = 0 to -4 V ID = -1 A		30		ns
Turn-off Delay Time *2	toff	VDD = -10 V, VGS = -4 to 0 V ID = -1 A		250		ns

Note) Measuring methods are based on JAPANESE INDUSTRIAL STANDARD JIS C 7030 Measuring methods for transistors.

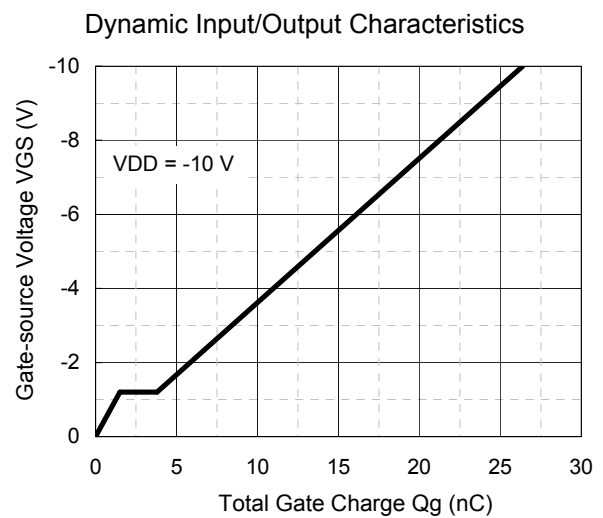
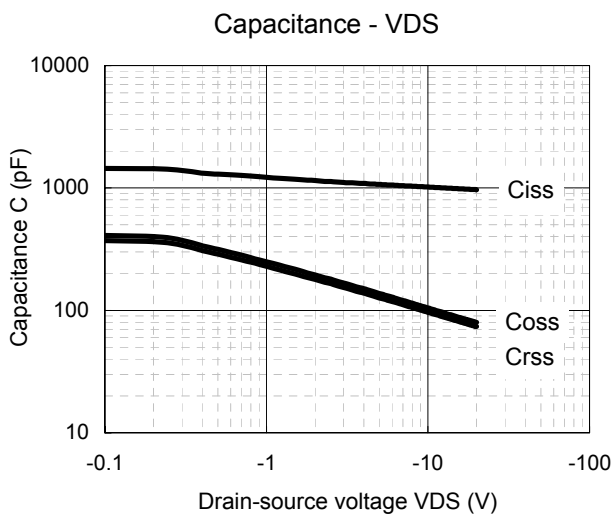
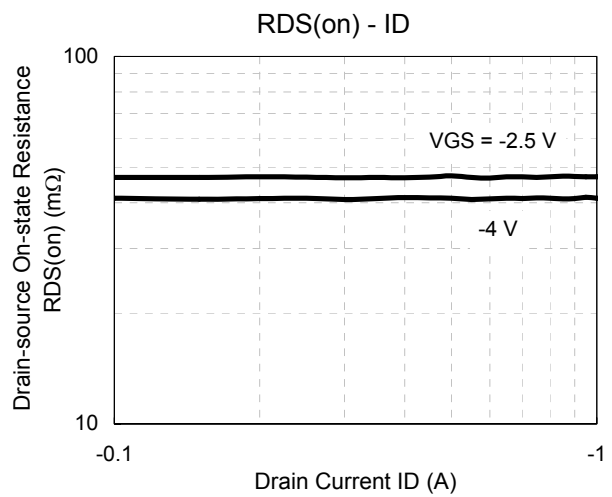
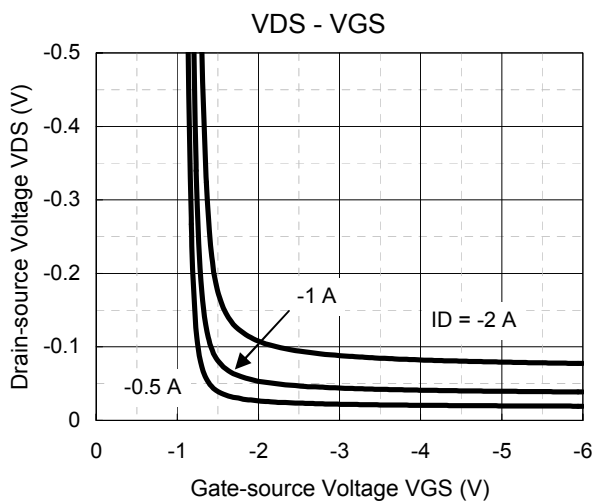
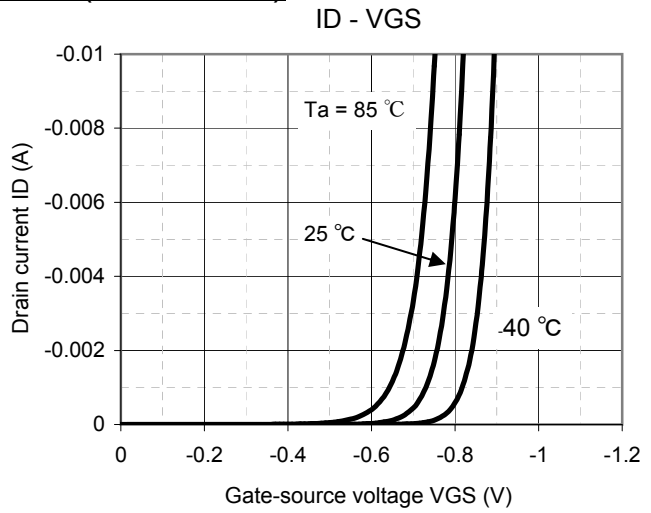
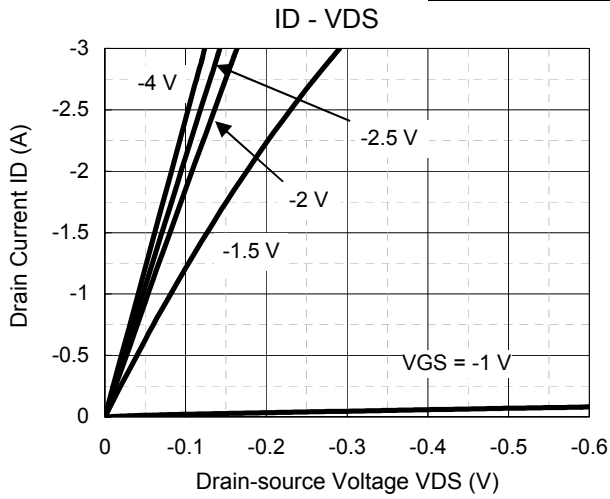
*1 Pulse test : Pulse width ≤ 300 μs, Duty cycle ≤ 2 %

*2 Measurement circuit for Turn-on Delay Time / Turn-off Delay Time

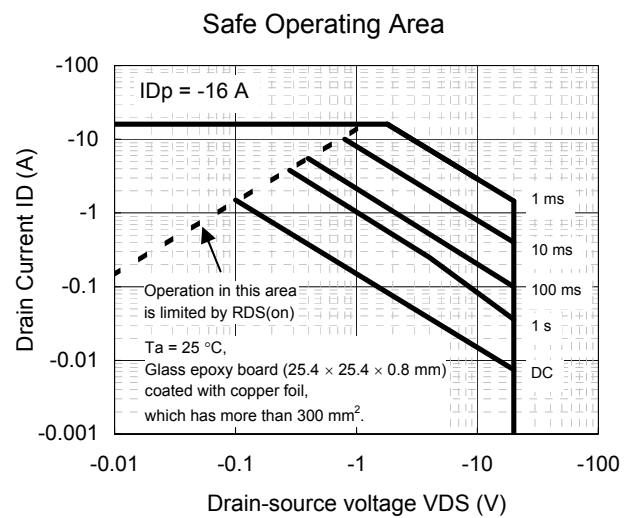
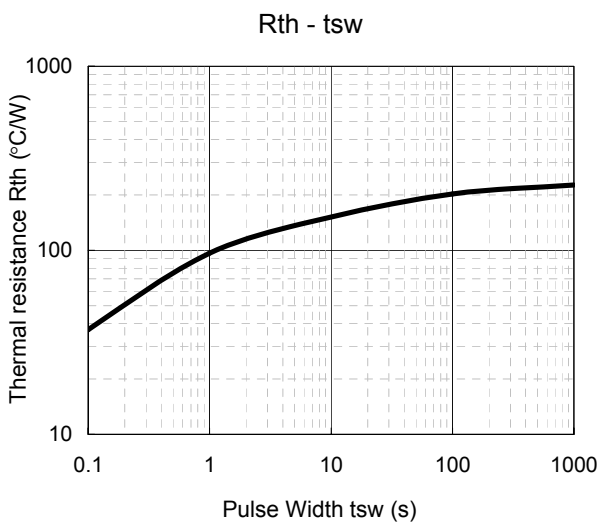
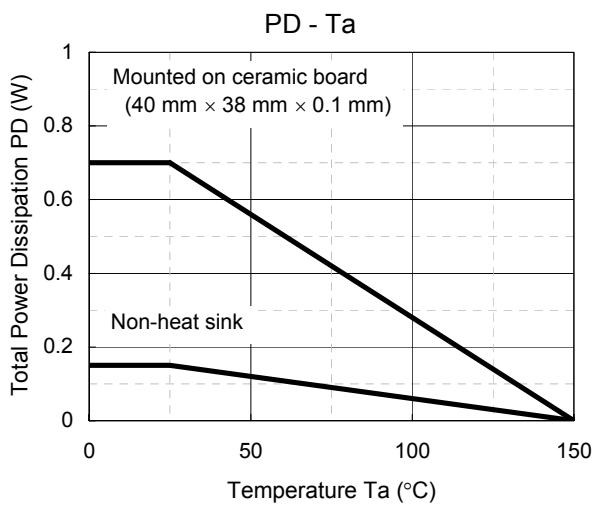
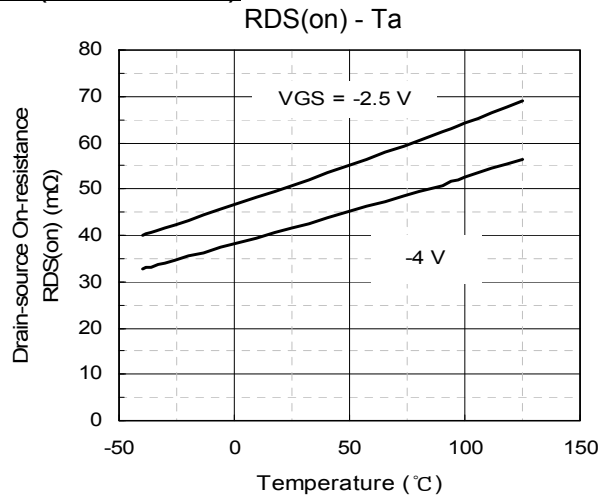
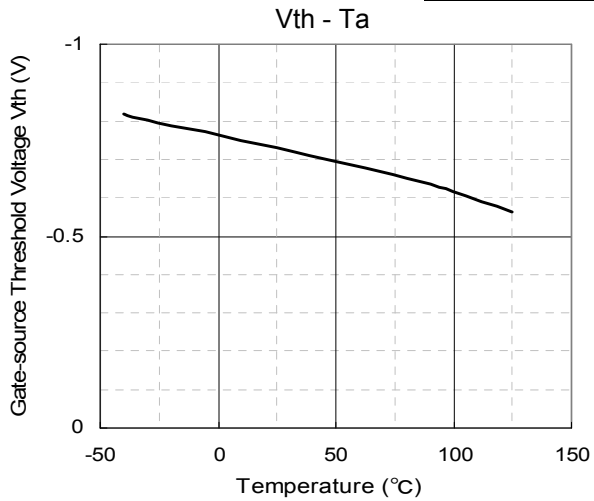
*2 Measurement circuit for Turn-on Delay Time / Turn-off Delay Time



Technical Data (reference)

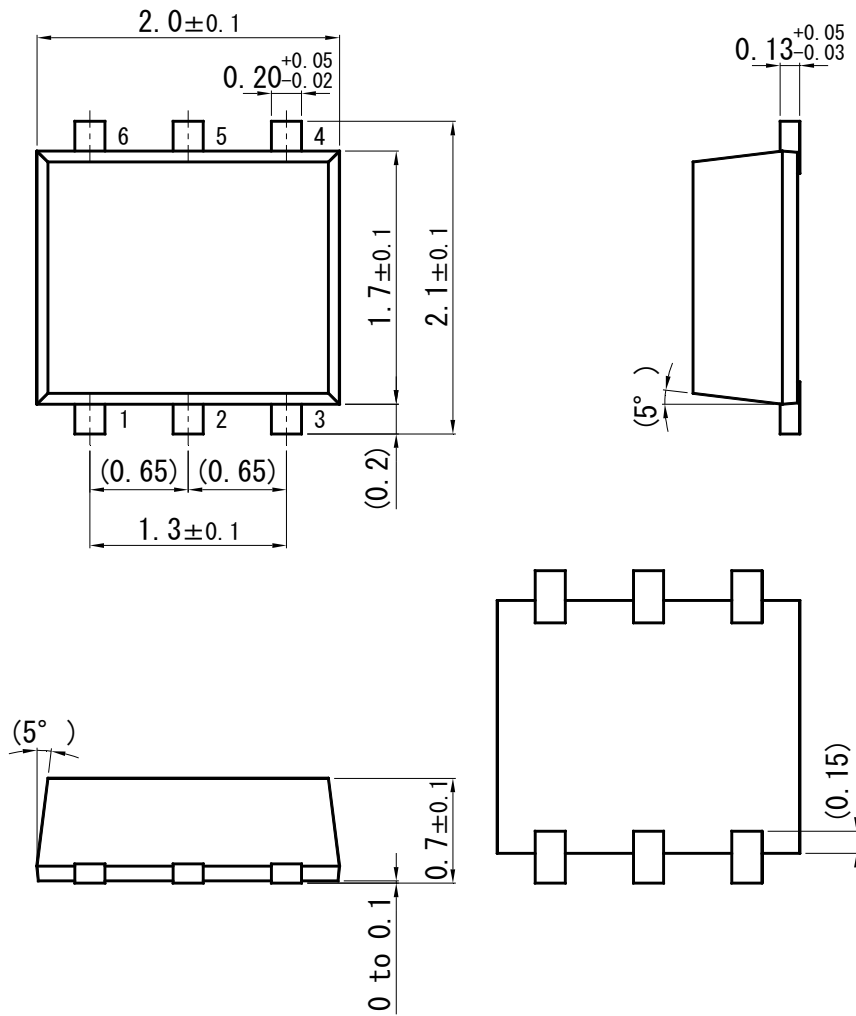


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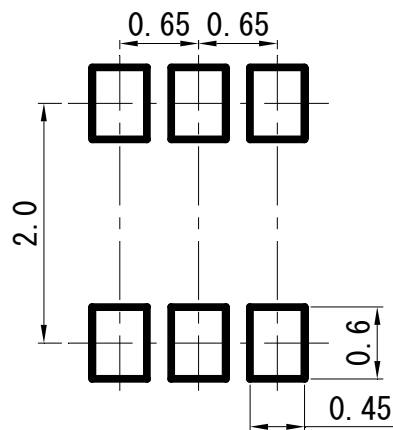


WSMini6-F1-B

Unit : mm



■ Land Pattern (Reference) (Unit : mm)



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